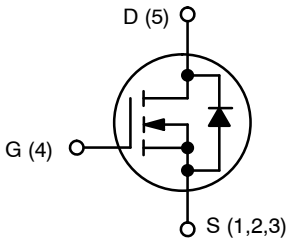
MOSFET - Power, Single N-Channel, STD Gate, SO8FL

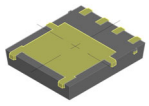
40 V, 0.6 mΩ, 384 A

NVMFWS0D63N04XM

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	0.6 mΩ @ V_{GS} = 10 V	384 A

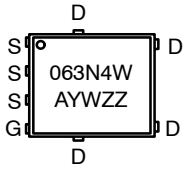
N−CHANNEL MOSFET





DFNW5 (SO−8FL)
CASE 507BA

MARKING DIAGRAM



063N4W = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain−to−Source Voltage		V_{DSS}	40	V
Gate−to−Source Voltage	DC	V_{GS}	±20	V
Continuous Drain Current	T_C = 25°C	I_D	384	A
	T_C = 100°C		271	
Power Dissipation	T_C = 25°C	P_D	157	W
Continuous Drain Current $R_{\theta JA}$	T_C = 25°C	I_D	60	A
	T_C = 100°C		42	
Pulsed Drain Current	T_C = 25°C, t_p = 10 μs	I_{DM}	900	A
Operating Junction and Storage Temperature Range		T_J, T_{STG}	−55 to 175	°C
Source Current (Body Diode)		I_S	131	A
Single Pulse Avalanche Energy	I_{PK} = 26.5 A	E_{AS}	585	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case (Note 2)	$R_{\theta JC}$	0.95	°C/W
Thermal Resistance, Junction−to−Ambient (Notes 1, 2)	$R_{\theta JA}$	39	

1. Surface mounted on FR4 board using 650 mm^2, 2 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	40			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA, Referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, T_J = 25°C			10	μA
		V_{DS} = 40 V, T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS						
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A, T_J = 25°C		0.54	0.6	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 230 μA, T_J = 25°C	2.5		3.5	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)}/\Delta T_J$	V_{GS} = V_{DS}, I_D = 230 μA		−7.24		mV/°C
Forward Trans−conductance	g_{FS}	V_{DS} = 5 V, I_D = 30 A		174		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		5862		pF
Output Capacitance	C_{OSS}			3760		
Reverse Transfer Capacitance	C_{RSS}			50		
Total Gate Charge	$Q_{G(TOT)}$	V_{DD} = 32 V, I_D = 50 A, V_{GS} = 10 V		92.2		nC
Threshold Gate Charge	$Q_{G(TH)}$			17.2		
Gate−to−Source Charge	Q_{GS}			25.8		
Gate−to−Drain Charge	Q_{GD}			17.4		
Gate Resistance	R_G	f = 1 MHz		0.60		Ω
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(ON)}$	Resistive Load, V_{GS} = 0/10 V, V_{DD} = 32 V, I_D = 50 A, R_G = 0 Ω		28		ns
Rise Time	t_r			9		
Turn−Off Delay Time	$t_{d(OFF)}$			47		
Fall Time	t_f			7.3		
SOURCE TO DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	I_S = 30 A, V_{GS} = 0 V, T_J = 25°C		0.78		V
		I_S = 30 A, V_{GS} = 0 V, T_J = 125°C		0.63		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, I_S = 50 A, dI/dt = 100 A/μs, V_{DD} = 32 V		83		ns
Charge Time	t_a			47		
Discharge Time	t_b			36		
Reverse Recovery Charge	Q_{RR}			246		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

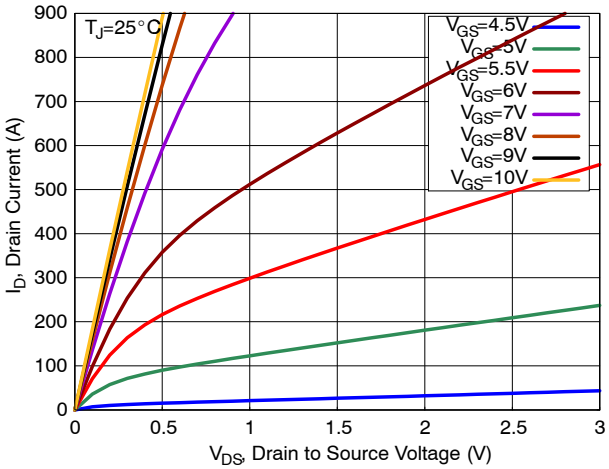


Figure 1. On−Region Characteristics

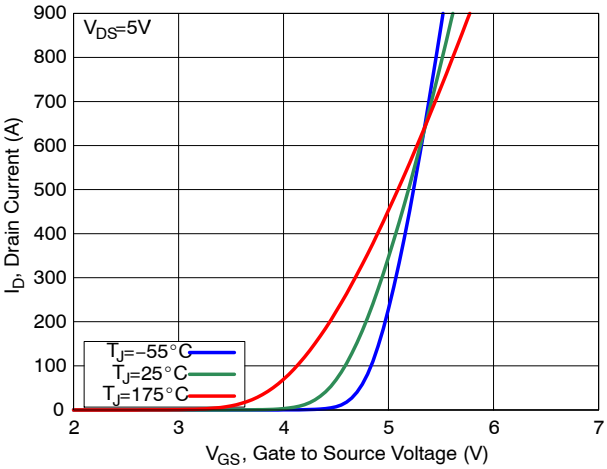


Figure 2. Transfer Characteristics

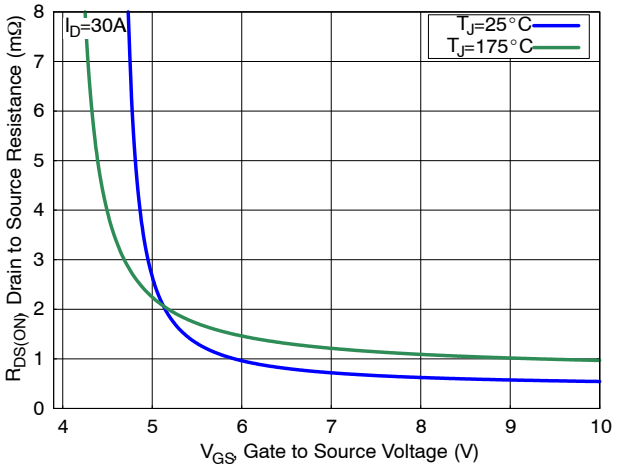


Figure 3. On−Resistance vs. Gate Voltage

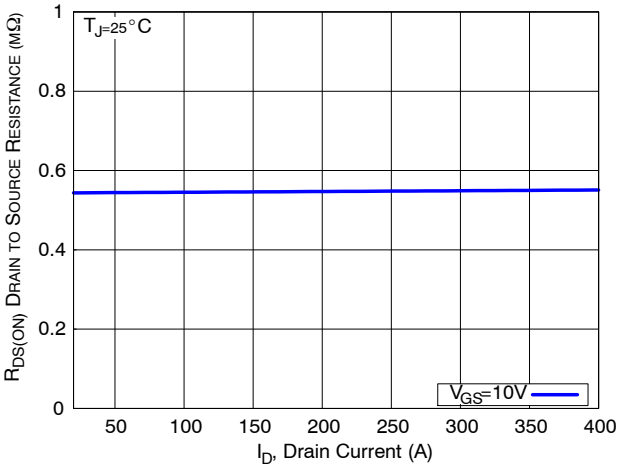


Figure 4. On−Resistance vs. Drain Current

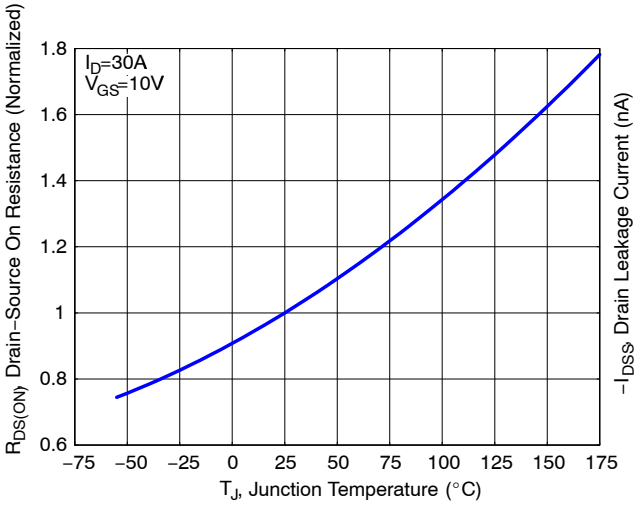


Figure 5. Normalized On−Resistance vs. Junction Temperature

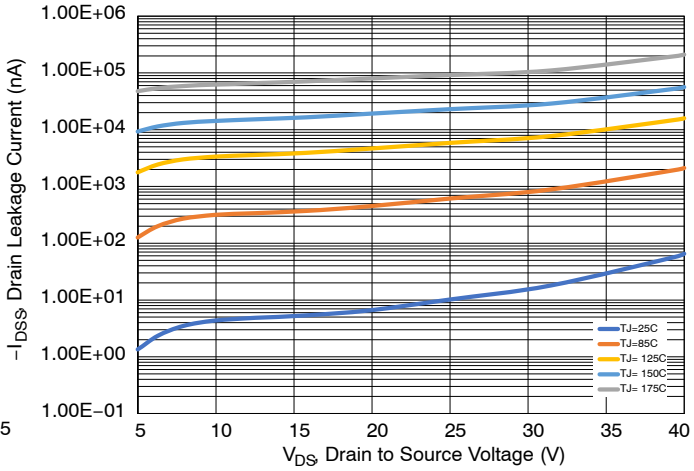


Figure 6. Drain−to−Source Leakage Current vs. Drain Voltage

TYPICAL CHARACTERISTICS (continued)

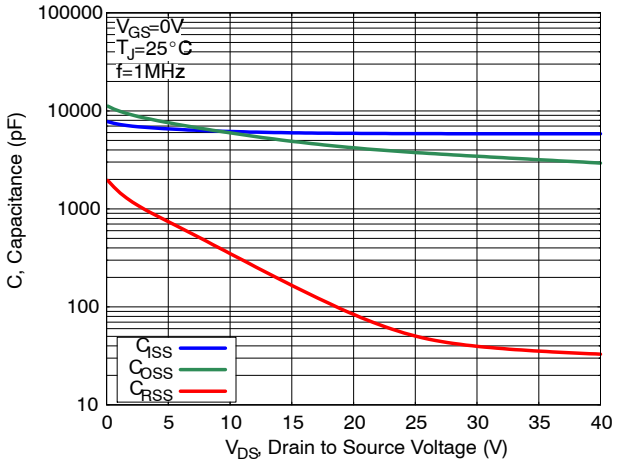


Figure 7. Capacitance Characteristics

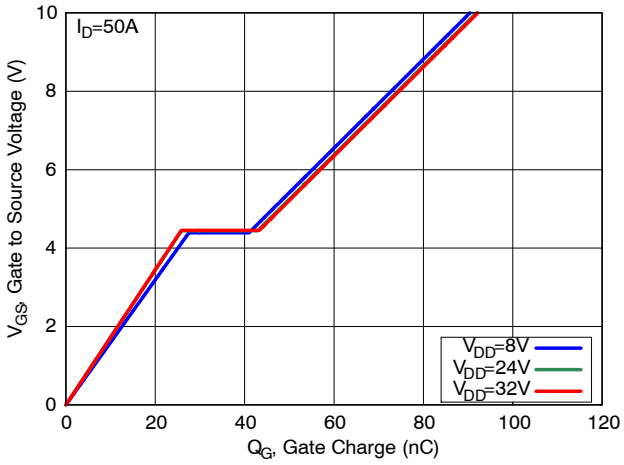


Figure 8. Gate Charge Characteristics

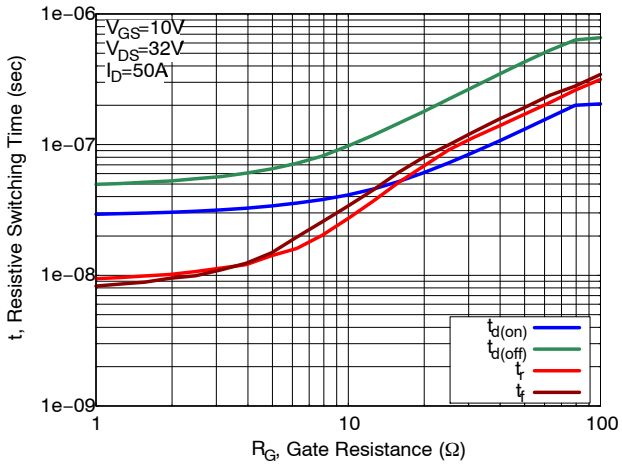


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

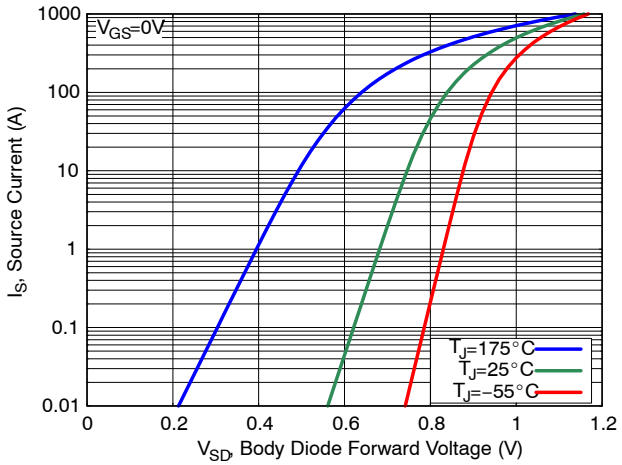


Figure 10. Diode Forward Voltage vs. Current

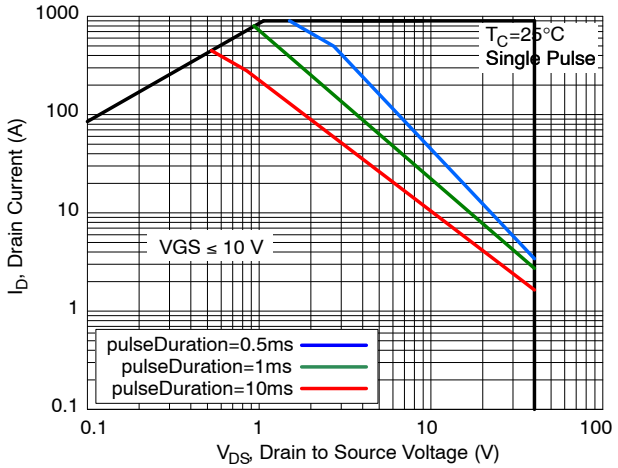


Figure 11. Safe Operating Area (SOA)

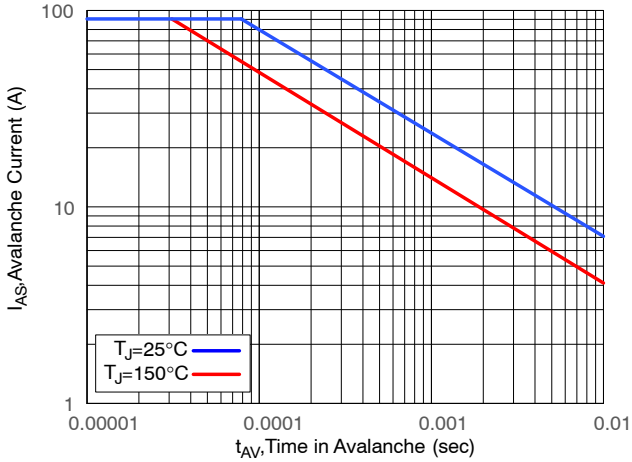


Figure 12. Avalanche Current vs. Pulse Time (UIS)

TYPICAL CHARACTERISTICS (continued)

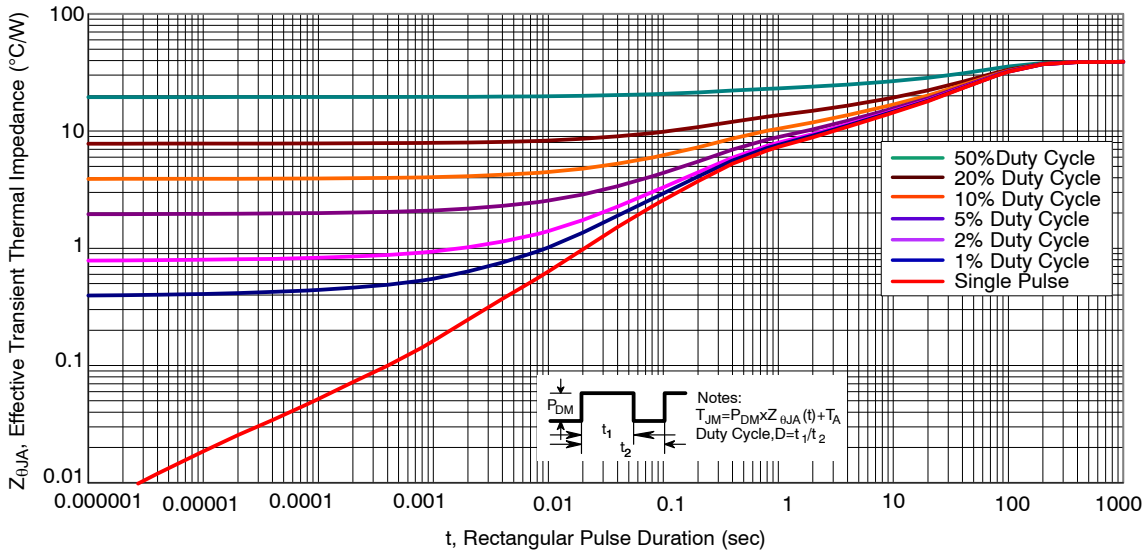


Figure 13. Thermal Characteristics

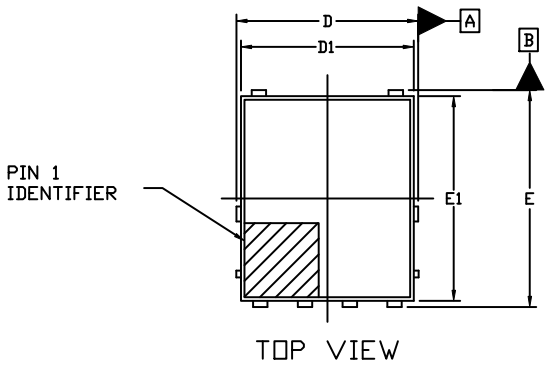
ORDERING INFORMATION

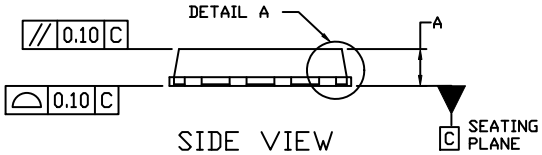
Device	Marking	Package	Shipping†
NVMFWS0D63N04XMT1G	063N4W	DFNW5 (Pb−Free)	1500 / Tape & Reel

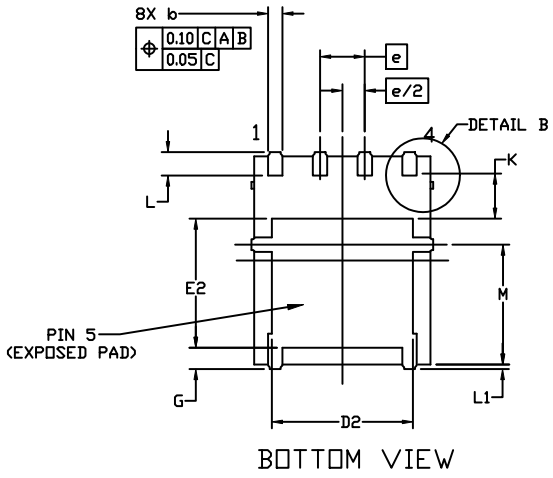
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

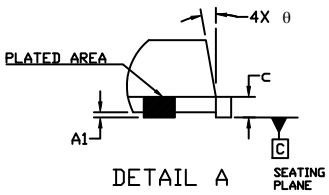
PACKAGE DIMENSIONS

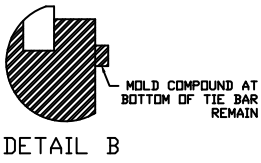
DFNW5 5x6 (FULL−CUT SO8FL WF)
CASE 507BA
ISSUE A





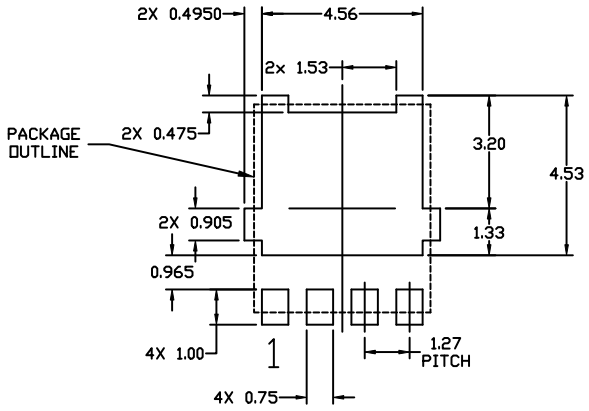






NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales